

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	New Application
				Filing Date	October 6, 2003
				First Named Inventor	Shunpei YAMAZAKI et al.
				Art Unit	2824
Examiner Name	M. Lebentritt				
Sheet	1	of	2	Attorney Docket Number	740756-2659

U.S. PATENT DOCUMENTS					
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
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Examiner Initials ¹	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁴
		Country Code ³ Number ⁴ Kind Code ³ (if known)				
MSL		JP6333824	12/02/1994			Abstract
MSL		JP6333825	12/02/1994			Full & Abstract
MSL		JP 03-229415	10/11/1991			Abstract
MSL		JP 06-333824	12/02/1994			Abstract

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Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MSL		DVURECHENSKII.A, TRANSPORT PHENOMENA IN AMORPHOUS SILICON DOPED BY ION IMPLANTATION OF 3D METALS, PP.635-640 PHYS. STAT. SOL.	
MSL		HAYZELDEN.C, IN SITU TRANSMISSION ELECTRON MICROSCOPY STUDIES OF SILICIDE-MEDIATED CRYSTALLIZATION OF AMORPHOUS SILICON, VOL.60/PP.225-227 APPL. PHYS. LETT.	
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Examiner Signature	<i>[Signature]</i>	Date Considered	12/20/04
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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				Application Number		New Application	
				Filing Date		October 6, 2003	
				First Named Inventor		Shunpei YAMAZAKI et al.	
				Art Unit		2854	
Examiner Name		M. Lebentritt					
Attorney Docket Number		740756-2659					
Sheet	2	of	2				

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Examiner Initials ^a	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
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Examiner Signature	<i>Markus Lebentritt</i>	Date Considered	12/20/04
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